

ABSTRACT

To resolve a problem that an etching rate profile is changed by a position of a nozzle relative to a semiconductor wafer and accordingly, at a vicinity of an outer edge of the semiconductor wafer, an accurate machining result is difficult to achieve, gas including activated species produced by plasma is blown from a nozzle locally to a surface of the semiconductor wafer W supported on a wafer table concentrically therewith to thereby remove unevenness on the surface of the semiconductor wafer. In this case, the wafer table is provided with a radius larger than a radius of the semiconductor wafer supported thereby by an outstretched portion to thereby prevent an outer edge from being removed excessively by reflected gas.